



BUK7S1R2-40H

N-channel 40 V, 1.2 mΩ standard level MOSFET in LFPAK88

28 September 2022

Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
 - -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package:
 - Designed for smaller footprint and improved power density over older wire bond packages such as D²PAK for today's space constrained high power automotive applications
 - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
 - Increased maximum current capability and excellent current spreading
 - Improved R_{DSon}
 - Low source inductance
 - Low thermal resistance R_{th}
- LFPAK Gull Wing leads:
 - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
 - Reduced cell pitch and superjunction platform enables lower R_{DSon} in the same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight $V_{GS(th)}$ limits enable easy paralleling of MOSFETs

3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

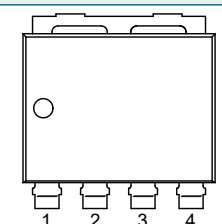
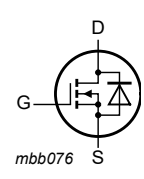
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	-	40	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 2}$	[1]	-	-	300	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$		-	-	294	W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	0.74	1.06	1.2	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 105\text{ °C}$; Fig. 12	1.05	1.59	1.9	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}$; $V_{DS} = 32\text{ V}$; $V_{GS} = 10\text{ V}$; Fig. 13 ; Fig. 14	-	14	28	nC
$Q_{G(tot)}$	total gate charge		-	80	112	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120\text{ A}$; $V_{sup} \leq 40\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; Fig. 4	[2] [3]	-	277	mJ
Source-drain diode						
Q_r	recovered charge	$I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$	[4]	-	38	nC

- [1] 300A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating emperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.
- [4] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;">LFPAK88 (SOT1235)</p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7S1R2-40H	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235
BUK7S1R2-40H/A002	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7S1R2-40H	7S1R240H
BUK7S1R2-40H/A002	7S1R240H

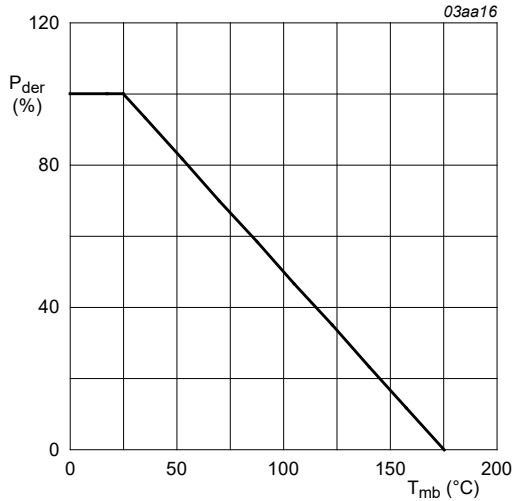
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

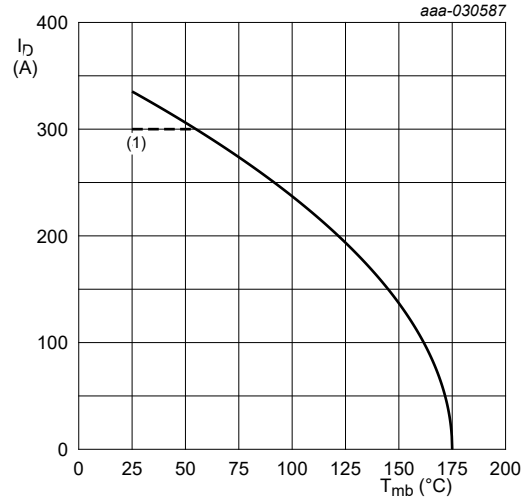
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	40	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175\text{ °C}$		-10	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1		-	294	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	[1]	-	300	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3		-	1341	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[2]	-	294	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	1341	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120\text{ A}$; $V_{sup} \leq 40\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; unclamped; Fig. 4	[3] [4]	-	277	mJ
I_{AS}	non-repetitive avalanche current	$V_{sup} \leq 40\text{ V}$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $R_{GS} = 50\text{ }\Omega$; Fig. 4	[5]	-	199	A

- [1] 300A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] 294A continuous current has been successfully demonstrated during application. Practically the current will be limited by PCB, thermal design and operating temperature.
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.
- [5] Protected by 100% test.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

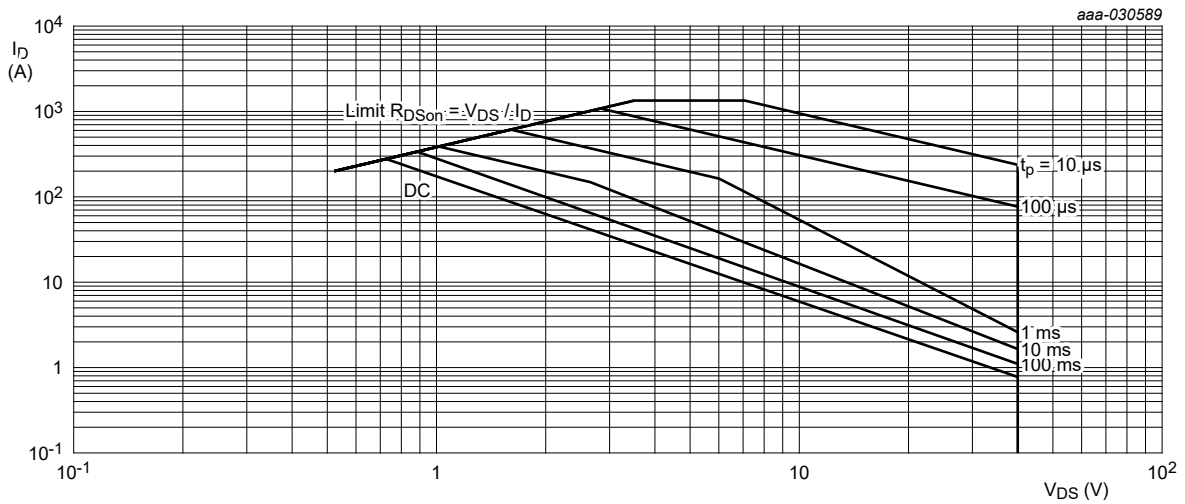
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

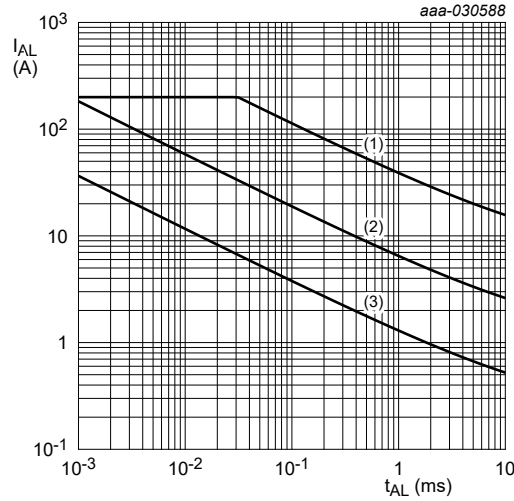
(1) 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; (2) $T_{j(\text{init})} = 150\text{ }^\circ\text{C}$; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.45	0.51	K/W

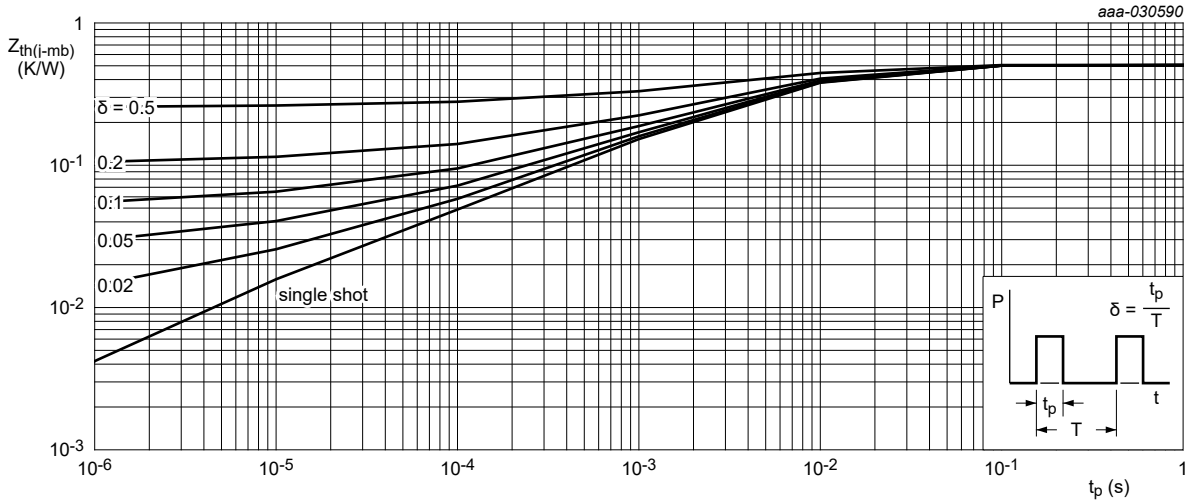


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	40	43	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_J = -40 \text{ }^\circ\text{C}$	-	40.5	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_J = -55 \text{ }^\circ\text{C}$	36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_J = 25 \text{ }^\circ\text{C};$ Fig. 9 ; Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_J = -55 \text{ }^\circ\text{C};$ Fig. 10	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_J = 175 \text{ }^\circ\text{C};$ Fig. 10	1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	0.06	1.2	μA
		$V_{DS} = 16 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 125 \text{ }^\circ\text{C}$	-	1.6	25	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 175 \text{ }^\circ\text{C}$	-	180	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 25 \text{ }^\circ\text{C};$ Fig. 11	0.74	1.06	1.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 105 \text{ }^\circ\text{C};$ Fig. 12	1.05	1.59	1.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 125 \text{ }^\circ\text{C};$ Fig. 12	1.16	1.76	2.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_J = 175 \text{ }^\circ\text{C};$ Fig. 12	1.46	2.21	2.6	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}; T_J = 25 \text{ }^\circ\text{C}$	0.4	1.05	2.6	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 13 ; Fig. 14	-	80	112	nC
Q_{GS}	gate-source charge		-	22	33	nC
Q_{GD}	gate-drain charge		-	14	28	nC
C_{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ Fig. 15 $T_J = 25 \text{ }^\circ\text{C};$	-	6014	8420	pF
C_{oss}	output capacitance		-	1352	1893	pF
C_{rss}	reverse transfer capacitance		-	244	537	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \text{ } \Omega$	-	19	-
t_r	rise time	-		16	-	ns
$t_{d(off)}$	turn-off delay time	-		50	-	ns
t_f	fall time	-		22	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_J = 25 \text{ }^\circ\text{C};$ Fig. 16	-	0.77	1	V
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}$	-	39	-	ns
Q_r	recovered charge		[1]	38	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
S	softness factor	$I_S = 25 \text{ A}$; $di_S/dt = -100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 20 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.82	-	
		$I_S = 25 \text{ A}$; $di_S/dt = -500 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 20 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.73	-	

[1] includes capacitive recovery

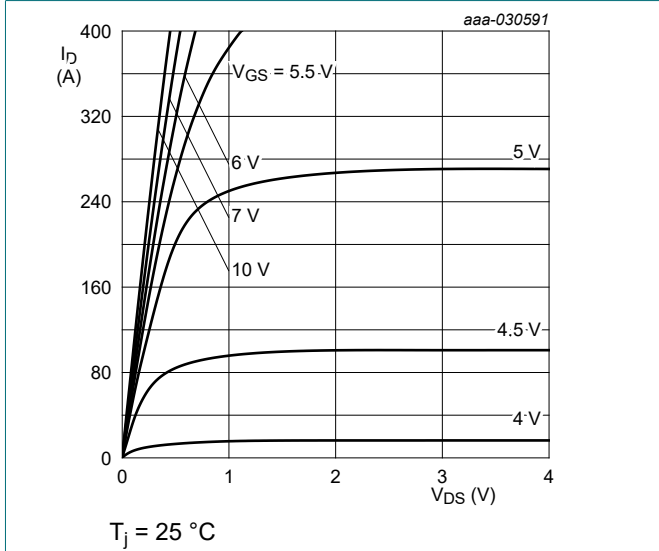


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

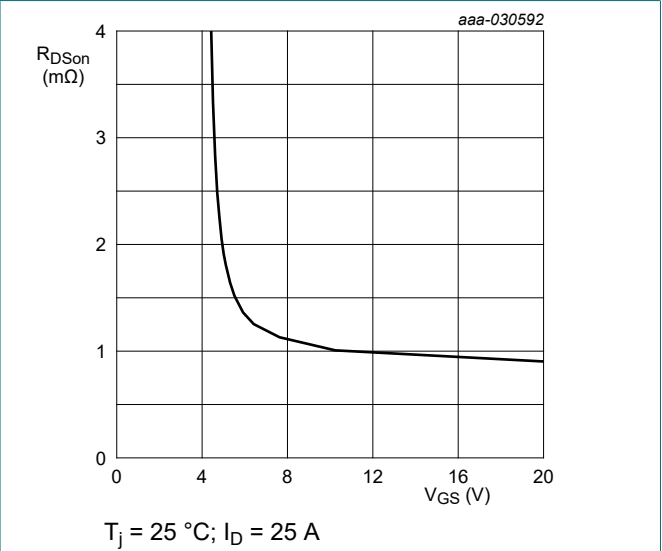


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

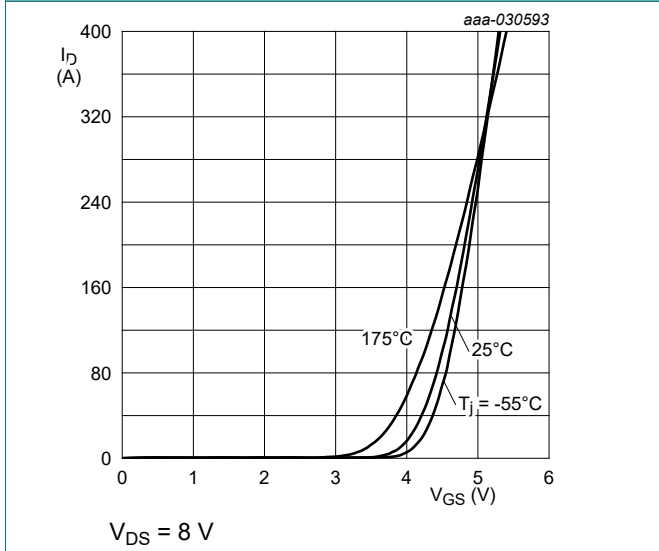


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

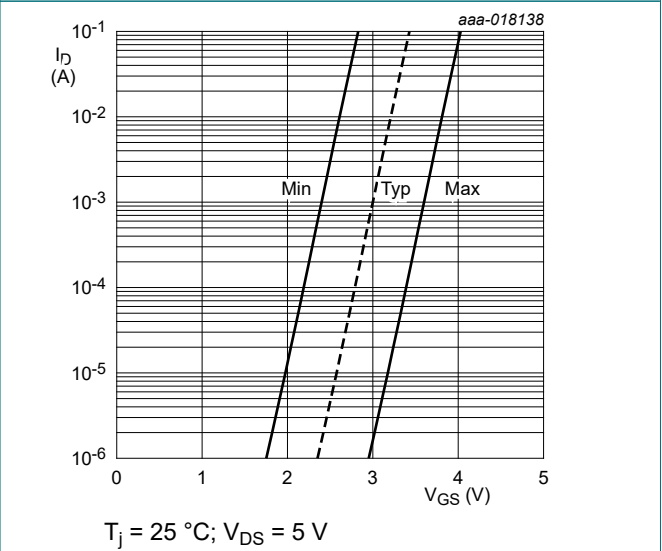


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

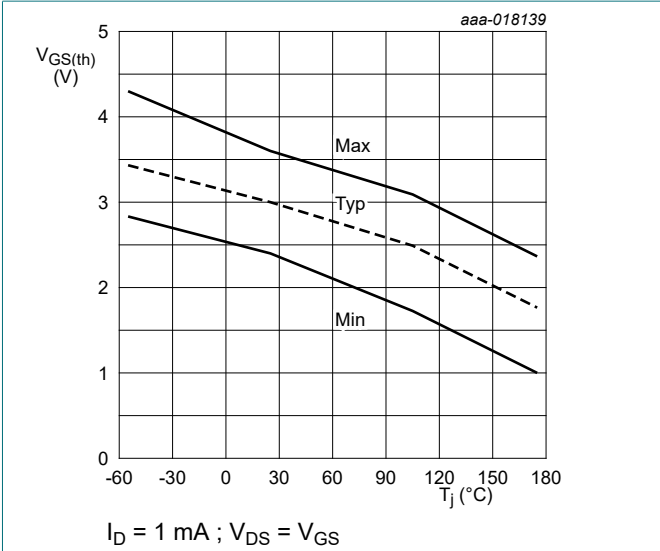


Fig. 10. Gate-source threshold voltage as a function of junction temperature

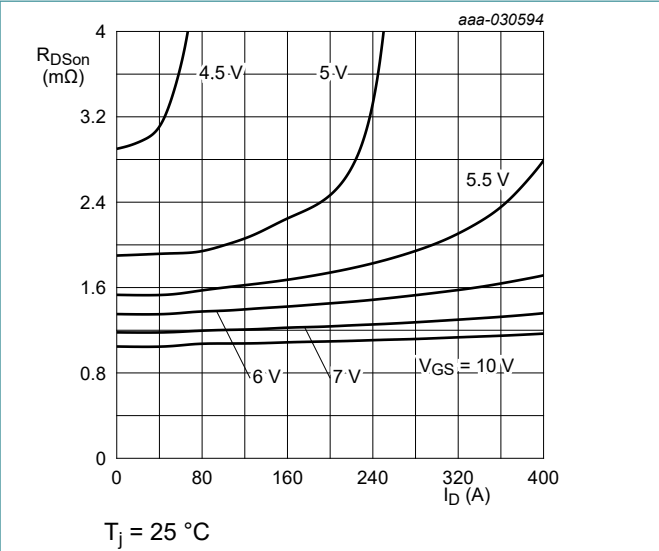


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

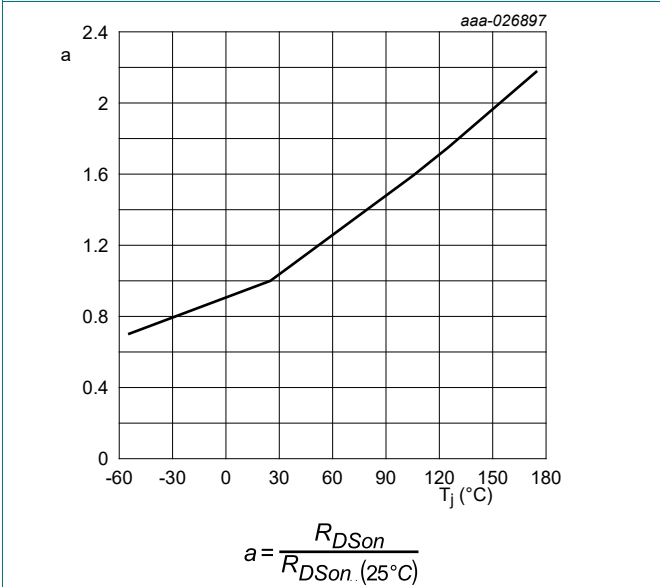


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

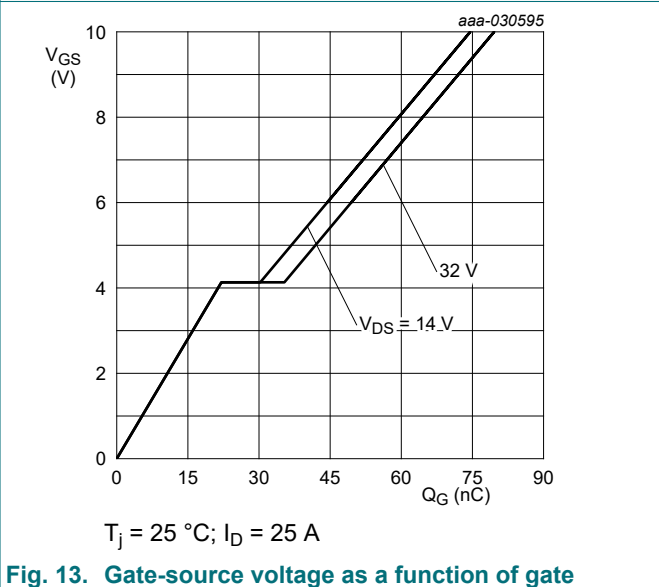


Fig. 13. Gate-source voltage as a function of gate charge; typical values

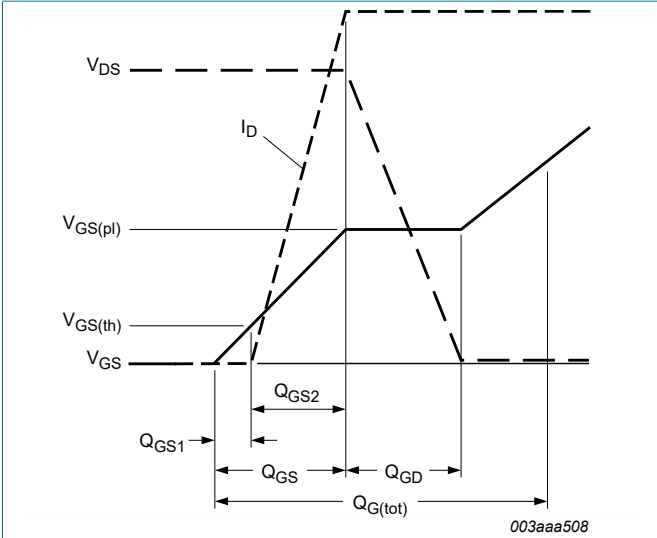


Fig. 14. Gate charge waveform definitions

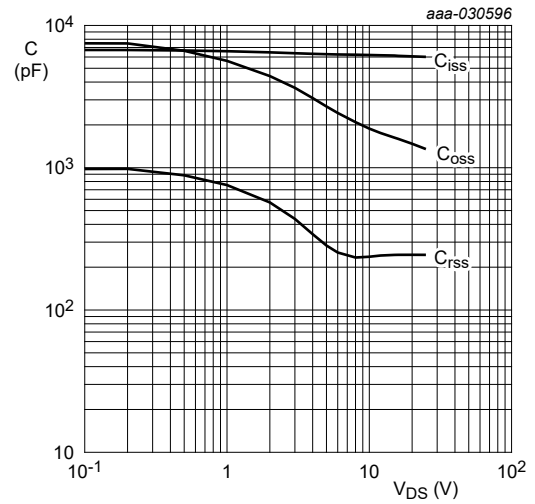
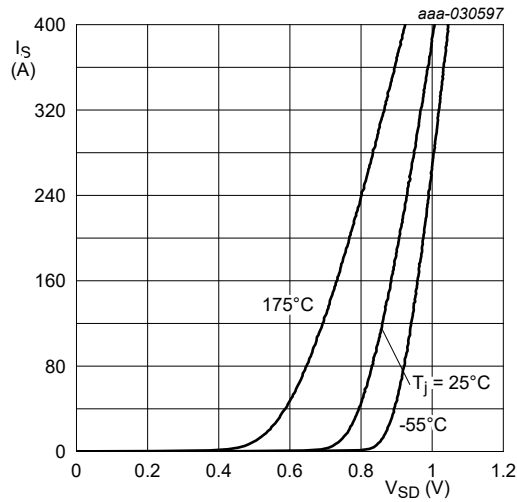


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values
 $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$



$V_{GS} = 0 \text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

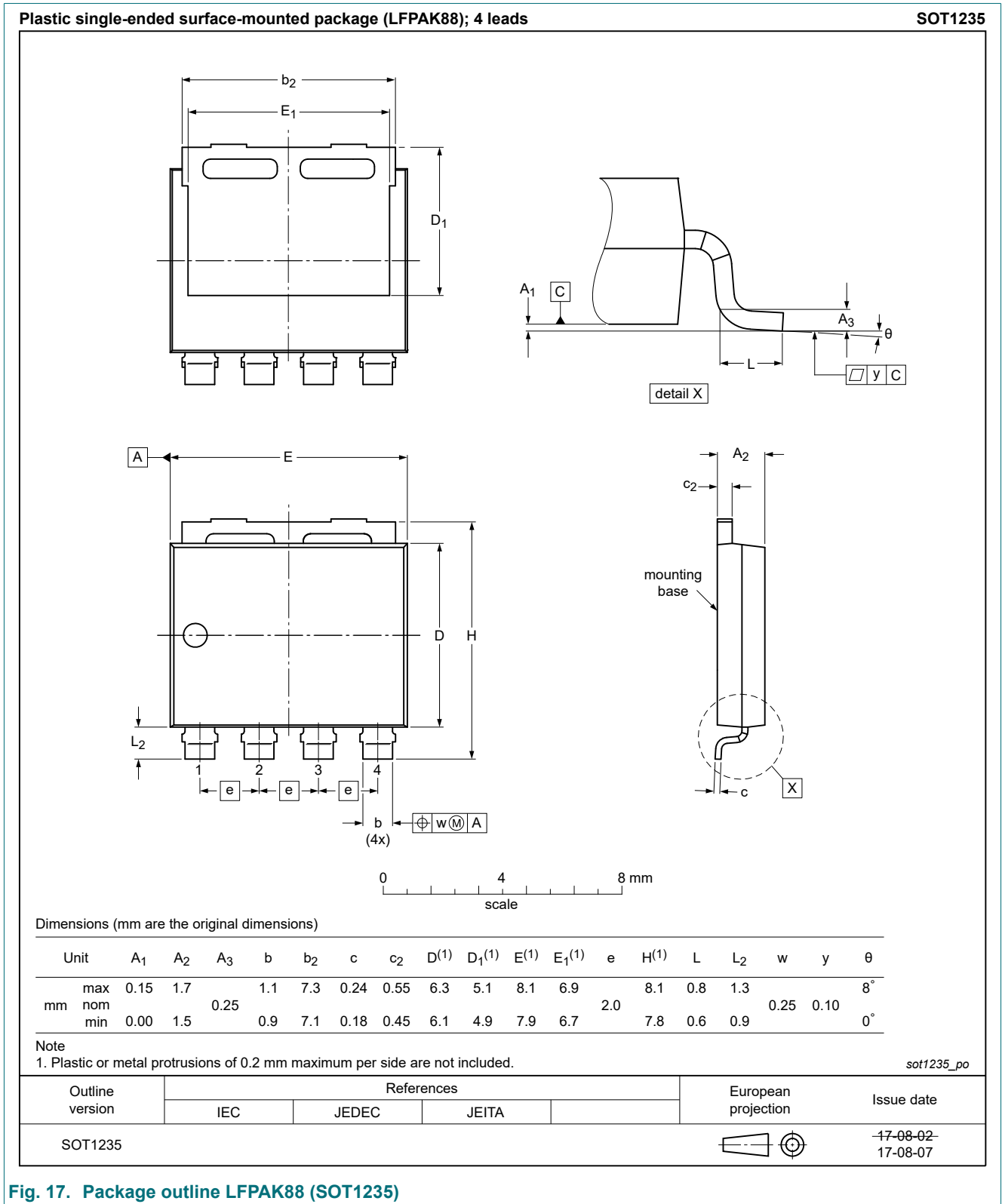


Fig. 17. Package outline LPAK88 (SOT1235)

12. Soldering

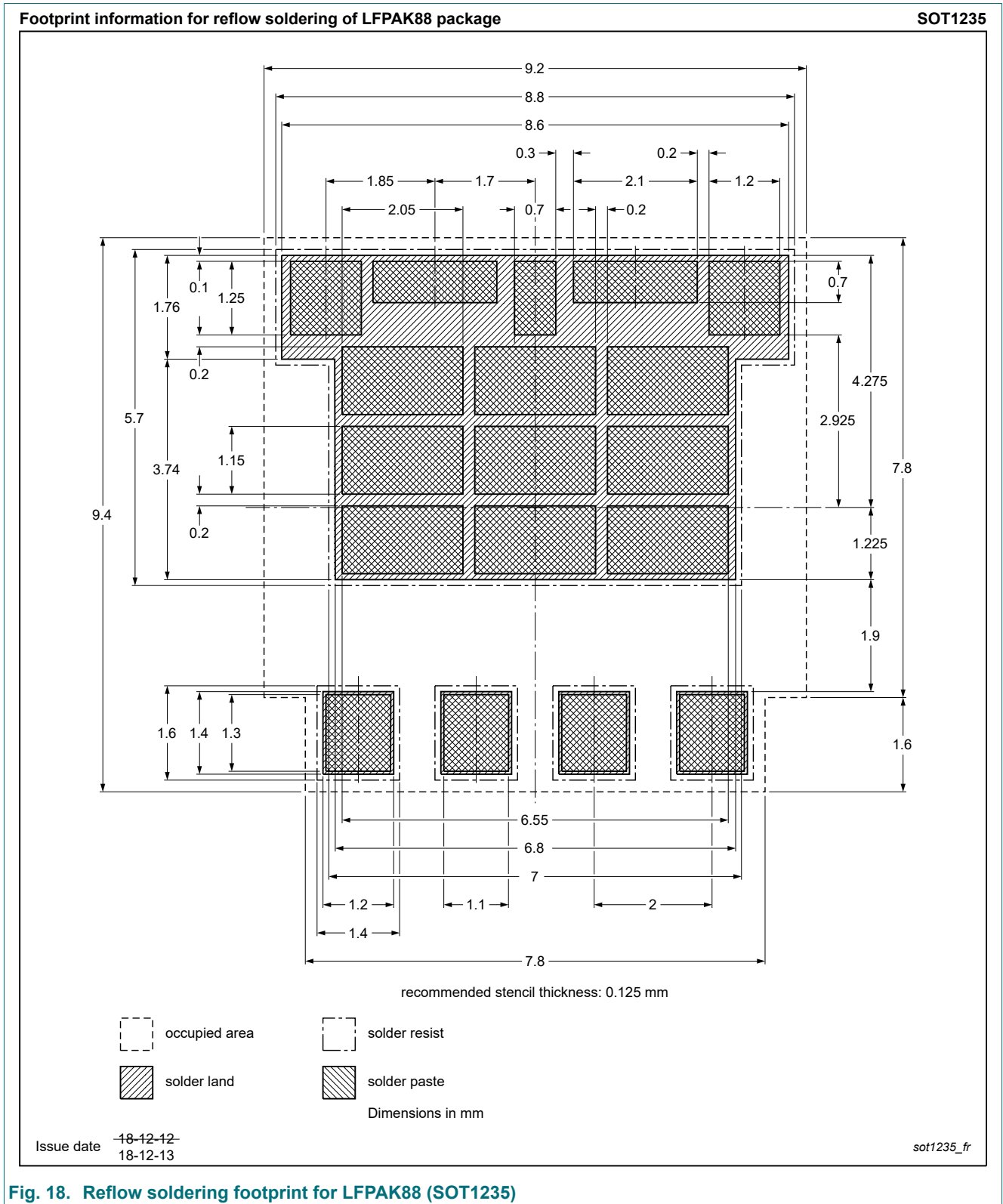


Fig. 18. Reflow soldering footprint for LPAK88 (SOT1235)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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